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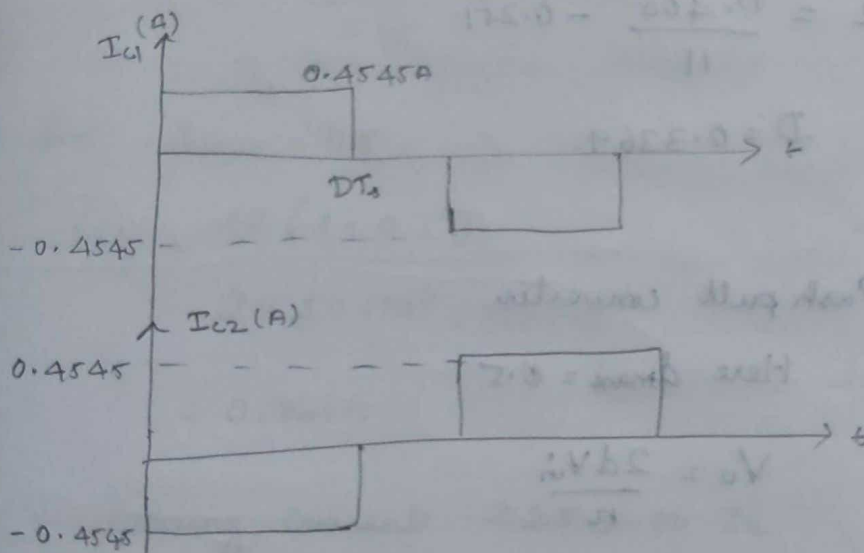
## EE6308D Switched Mode & Resonant Converters.

### Test - 2

2) For the current in the capacitors  $33\mu F$ ,

$$I_{C1} = -I_{C2}$$

$$I_{C1} = \frac{I_o}{2n} = \frac{10}{2 \times 11} = 0.4545 A$$



Here given is ideal so

$$V_o = \frac{DV_{in}}{n}$$

$$12 = \frac{D \times 400}{11}$$

$$D = 0.33$$

$$DT_s = \frac{0.33}{25 K} = 13.2 \mu s$$

b). 3% leakage inductance

$$0.03 \times 2.7 \text{ mH} = 81 \mu\text{H}$$

$$\text{Voltage loss} = \left( \frac{3}{2} f_s \frac{L_l}{n^2} \right) I_o$$

$$= \frac{1.5 \times 25 \times 10^3 \times 81 \times 10^{-6}}{11^2} \times 10.$$

$$\approx 0.251 \text{ V}$$

$$V_o = \frac{D V_{in}}{n} - V_{\text{loss}}$$

$$12 = \frac{D \cdot 400}{11} - 0.251$$

$$D = 0.3369.$$

6.

Push pull converter

$$\text{Here } d_{\text{max}} = 0.5$$

$$V_o = \frac{2d V_{in}}{n}$$

$$48 = \frac{2 \times 0.5 \times 200}{n}$$

$$n = 4.166 \approx 4.$$

$$d_{\text{min}} \Rightarrow \frac{2d V_{in}}{n} = V_o$$

$$\frac{2 \times d \times 200}{4} = 48.$$

$$d_{\text{min}} = 0.3428$$

$$I_{LP-P} = \frac{V_o (1-d) T_s}{2L}$$

$$1 = \frac{48(1-0.3428) \times 1}{2 \times 0.50 \times 10^{-3} \times L}$$

$$L = 315 \mu H$$

$$\Rightarrow ESR \times 1 = 0.48$$

$$\therefore ESR = 0.48 \Omega$$

Using  $30 \mu s$  fanily

$$C = \frac{30 \mu}{0.48} = 62.5 \mu F$$

For  $d_{max} = 0.5$ ,

$$I_{LPP} = \frac{48(1-0.5)}{2 \times 50 \times 10^{-3} \times 315 \times 10^{-6}}$$

$$= 0.7619$$

Magnetizing current  $= 25\% \text{ of } I_L$

$$= 0.25 \times 5$$

$$= 1.25 A$$

$$d = \frac{V_{in} d T_s}{2Lp}$$

$\Rightarrow$  take  $d = 0.3428$

$$V_{in} = 280$$

$$= \frac{280 \times 0.3428 \times 1}{2 \times 315 \times 10^{-6} \times 50 \times 10^{-3}} = 0.544126$$

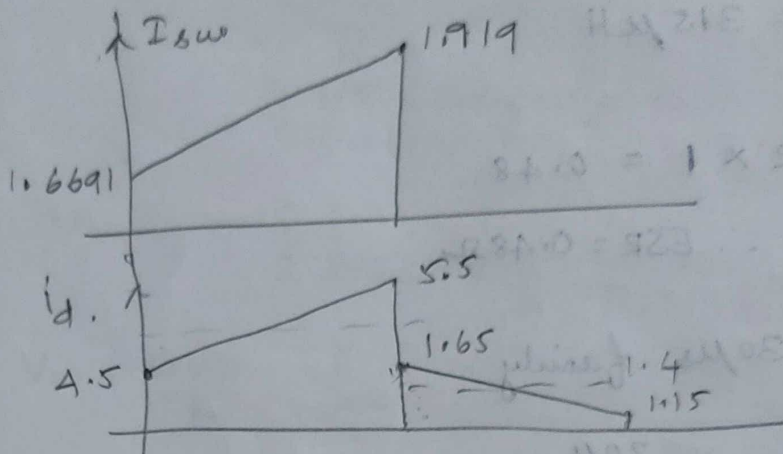
We take  $I = 5 A$

$$\Delta I_{Lpp} = 1 A$$

$$b = \frac{5}{2} + \frac{1}{2} = 3 A$$

We select  $i_{p1}$  because it will be maximum

$$C = 4.5 A$$



switch current rating

$$\text{Peak current} = 1.919 A$$

$$\text{Rms current} = \frac{(1.669 + 1.919) \sqrt{0.3428}}{2}$$

$$= 1.0503 A$$

$$\text{Average current} = \frac{(1.669 + 1.919)}{2} \times 0.3428$$

$$= 0.6149 A$$

$$\text{diode rms current} = \sqrt{5^2 \times 0.3428 + 1.4^2 (0.5 - 0.3428)}$$

$$= 2.9796 A$$

for Transformer.

Area product  $\Rightarrow$



$$\text{Primary rms current} = 1.0503 \text{ A}$$

$$A_p = \frac{1.0503}{3} = 0.3501 \text{ m}^2$$

$$\text{secondary rms current} = 2.9796 \text{ A}$$

$$A_s = \frac{2.9796}{3} = 0.993 \text{ mm}^2$$

$$K_s A_w = n_p \times 0.3501 + n_s \times 0.993$$

$$A_w = \frac{n_p}{K_s} \left[ 0.3501 + \frac{0.993}{k} \right] = 0.59835 \frac{n_p}{K_s}$$

$$n V_o T_s = B_m A_c n_p$$

$$A_c = \frac{4 \times 48 \times 10^6}{50 \times 10^3 \times n_p \times 0.2}$$

$$= \frac{19200}{n_p}$$

$$A_p = \frac{11488.32}{K_s} = 32823 \text{ mm}^4$$

We select E47/20/16. ~~not~~

Inductor design

$$K_i = \left( 1 + \frac{0.20}{2000} \right) = 1.1$$

$$A_p = \frac{1}{2} \times 315 \times 10^{-6} \times 5^2 \times \frac{2 \times 1.1 \times 10^6}{0.35 \times 3 \times 0.2}$$

$$= 41250.$$

We use same E47/20/16

1. Design equation for an inductor with DC Bias

$$\text{Maximum flux linkage} = LI_p$$

$$\therefore A_c B_{\max} N \text{ must be } \geq LI_p$$

Where  $A_c$  = area of cross section of core =  $A_e$  of core

$$\therefore A_c \geq \frac{LI_p}{N B_{\max}}$$

$$\text{i.e., } A_c \geq \frac{K_i LI}{N B_{\max}} \text{ where } K_i \text{ is as follows}$$

$$K_i = \left( 1 + \frac{P - P_{\text{ripple}} (\%) }{200} \right)$$

Let  $J$  be the chosen design current density value. Usually it is between  $2 \text{ A/mm}^2$  to  $3 \text{ A/mm}^2$

$$\therefore \text{Wire copper Area} = \frac{(I_{\text{rms}})}{J} = \frac{I}{J} \text{ mm}^2$$

Window area need for  $N$  turns with spacing factor accounted

$$A_w = \frac{NI}{K_s J} \text{ with } K_s \text{ between } 0.3 \text{ to } 0.45$$

$\therefore$  Area product needed

$$\text{in the core} = A_p = A_c A_w = \frac{K_i}{K_s} \cdot \frac{LI^2}{J B_{\max}}$$

$$= \left( \frac{1}{2} LI^2 \right) \left( \frac{2 K_i}{K_s J B_{\max}} \right)$$

from the above equation, we get  
size of core is  $\propto$  Magnetic energy storage  
for DC current

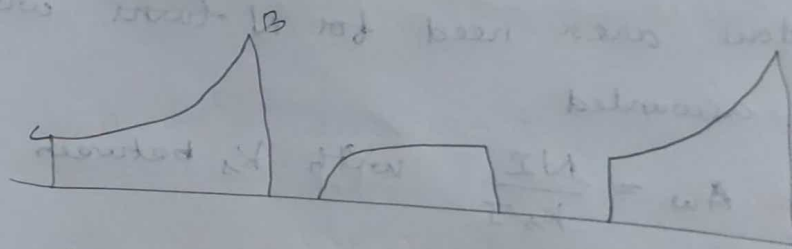
$N \rightarrow$  not there in  $A_p$

small  $N \rightarrow A_c \uparrow, A_w \downarrow$

large  $N \rightarrow A_c \downarrow, A_w \uparrow$ .

### 5) Flux walking problem:

Upward travel amount of  $B$  will be different from downward travel amount of  $B$ . Hence  $B$  will either climb towards the saturation (or) towards negative saturation with time. This is called flux walking problem. Now the supply current takes on slope as follows



current reach stable shapes when  
volt-sec loss is path reactances of the  
path which had a higher volt-sec applied  
to it reaches such a value that the  
net volt-sec in the other path. The



resulting current unbalance obviously depends on resistances in the path leads to damage of switches

### Solutions

- i) Handle it problem - source level  $\rightarrow$  pay attention to ascertain symmetry of elements. Minimise the difference between duty ratio in two half cycles.
- ii) Keep identical turns in primaries & secondaries.
- iii) Use matched diodes from same package.
- iv) Use identical gate drive circuits

### External Measures.

- a) gapping the core.
- b). Match switches & avoid BJTs & used MOSFETs
- c) Add primary resistance
- d) Use current mode control.



$$7). V_o = \frac{2dV_{in}}{n}$$

for  $D = ?$

$$V_{in} = 180V$$

$$12 = \frac{2 \times d \times 180}{6}$$

$$d = 0.2$$

$$V_{in} = 240$$

$$12 = \frac{2 \times d \times 240}{6}$$

$$d = 0.15$$

$d$  vary from 0.15 to 0.2.

take maximum value of  $I$  as 10A

$$V = 10 \times 0.4 = 4V$$

take  $V_{fw} = 1$ .

$$nL_m \geq \frac{100 d_{max} (V + V_{fw})}{\times f_s \times I}$$

here take  $x = 1$

$$nL_m = \frac{100 \times 0.2 (4 + 1)}{20 \times 10^3 \times 10}$$

$$nL_m = 500 \mu H \rightarrow T$$

$$B_m = \frac{D_{max} (V + V_{sw})}{\times f_s \times A_c}$$

$$= \frac{0.2 (4 + 1)}{1 \times 20 \times 10^3 A_c} = \frac{50 \mu}{A_c}$$

	$n$	$I_{rms}$	$B_m \text{ wb/m}^2$
$T_{10}$	654		
$T_{12}$	424		
$T_{16}$	337		
$T_{20}$			
$T_{32}$	206	0.0217	0.008196

Let  $J = 2.5 \text{ A/mm}^2$

$$I_{rms} = \frac{P_o}{n} \sqrt{d_{max}}$$

$$A = \frac{0.0217}{2.5} = 0.0086$$

We select  $T_{32}/206 \text{ T/SWG 19}$ .

$$V_z = \frac{d_{max}}{1 - d_{max}} (V + V_{fw}) - V_{fw}$$

$$= \frac{0.2}{1 - 0.2} (4 + 1) - 1$$

$$= 0.25 \text{ V}$$

We select standard as 2.4V.

Power rating of Zener diode

$$= \frac{I_m I_m}{2} f_s$$

$I_m$  as 1% of  $I_{max}$

$$= \frac{1 \times 10^{-6} \times (0.1)^2 \times 20 \times 10^3}{2}$$

Take  $I_m = 1 \mu\text{H}$

$$= 0.1 \text{ W}$$

If 1mH then power rating = 0.1W.

$$R_s = \frac{nV}{I} = \frac{206 \times 4}{10} = 82.4 \Omega$$

$$R_s \text{ power loss} = \frac{(4 \times \sqrt{0.2})^2}{82.4}$$

$$= 0.0388 \text{ W.}$$

so we take  $R_s$  as  $82.4 / \frac{1}{4} \text{ W.}$

4. Output power of full bridge converter is twice as half bridge converter. To derive the half bridge.

$$i_{s1 \text{ rms}} = 0.5 I_o \sqrt{2d+1}$$

$$i_{p \text{ rms}} = \sqrt{2d} I_o / n.$$

$$P_{in} = \text{Avg of } V_p i_p = \frac{V_{in} I_o}{n} d.$$

$$P_o = \eta P_{in} = \eta \frac{d V_{in} I_o}{n}.$$

$$\Rightarrow \frac{V_{in}}{2} d T_s = 2 A_c B_{max} \eta P$$

$$d V_{in} = 4 A_c B_{max} \eta P f_s$$

$$P_o = \frac{\eta}{n} 4 A_c B_{max} \eta P f_s I_o$$

Area product

$$\eta P \frac{\sqrt{2d} I_o}{n} + 2 \times \frac{0.5 I_o \sqrt{2d+1}}{n} n_s = K_s A_w$$

$$I_o \frac{n_p}{n} = \frac{K_s A_w f_s}{\sqrt{2d+1}}$$



$$\therefore P_o = \left( \frac{4}{\sqrt{2d} + \sqrt{2d+1}} \eta B_{max} J f_s K_s \right) A_c A_w$$

$$\text{if } d = 0.5$$

$$P_o = (1.72 \eta B_{max} J f_s K_s) A_c A_w$$

This is for half bridge converter, for full bridge converter,

$$P_{o_{full}} = 2 P_{o_{half}}$$

$$P_{o_{full}} = (3.44 \eta B_{max} J f_s K_s) (A_c A_w)$$

3. CCM and DCM flyback operation:

Trf becomes much bigger than in DCM.

Reason: Nearly 1:2 input voltage range and 1:10 load current range requiring a large  $L_p$  to keep converter in CCM

→ Large load range is better accommodated in a DCM design

→ The size of inductor in CCM will be larger than that of DCM design for same power output

→ current stress in devices will be lesser in CCM design